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Product data sheet

#### 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Ultra thin package profile of 0.37 mm

#### 3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-30	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-1	А
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -1 A; T <sub>j</sub> = 25 °C		-	430	510	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.





30 V, P-channel Trench MOSFET

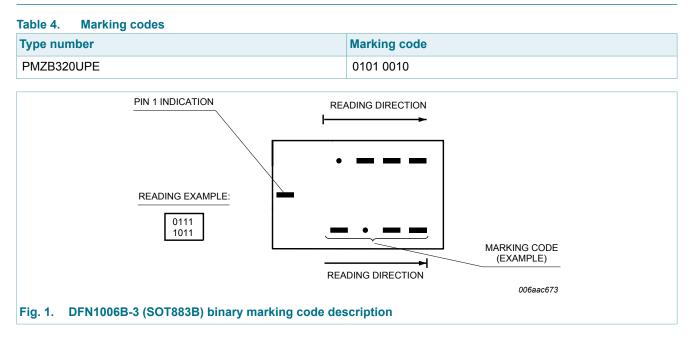
#### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G G S 017aaa259

#### 6. Ordering information

Table 3. Ordering in	formation					
Type number	Package	ge				
	Name	Description	Version			
PMZB320UPE	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

## 7. Marking



30 V, P-channel Trench MOSFET

#### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-30	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C	[1]	-	-1	А
		$V_{GS}$ = -4.5 V; $T_{amb}$ = 100 °C	[1]	-	-0.6	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-4	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	350	mW
			[1]	-	760	mW
		T <sub>sp</sub> = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode	,				
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-0.7	А

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

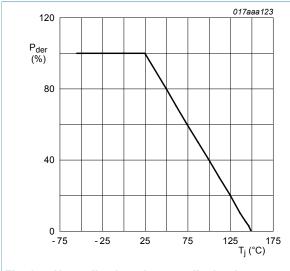
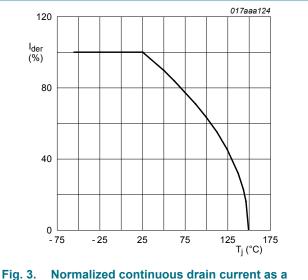
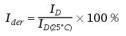


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



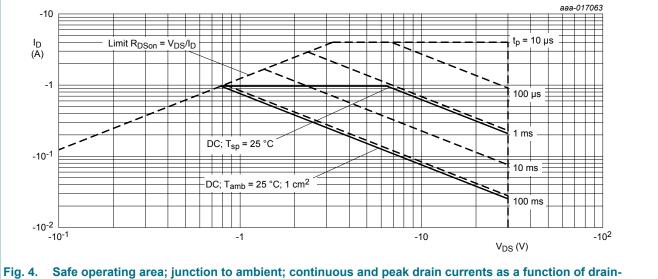
function of junction temperature



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#### 30 V, P-channel Trench MOSFET



source voltage

#### 9. Thermal characteristics

#### Table 6. Thermal characteristics

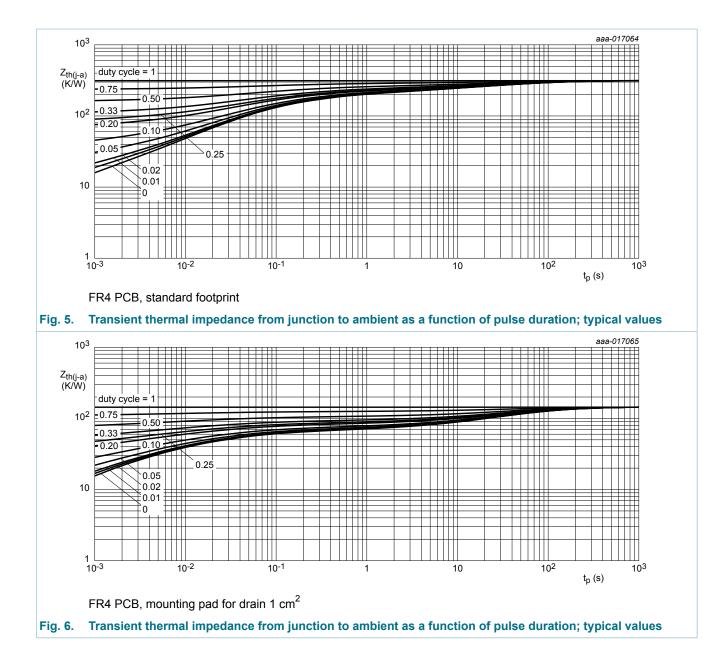
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	315	360	K/W
			[2]	-	145	165	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	17	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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#### 30 V, P-channel Trench MOSFET



30 V, P-channel Trench MOSFET

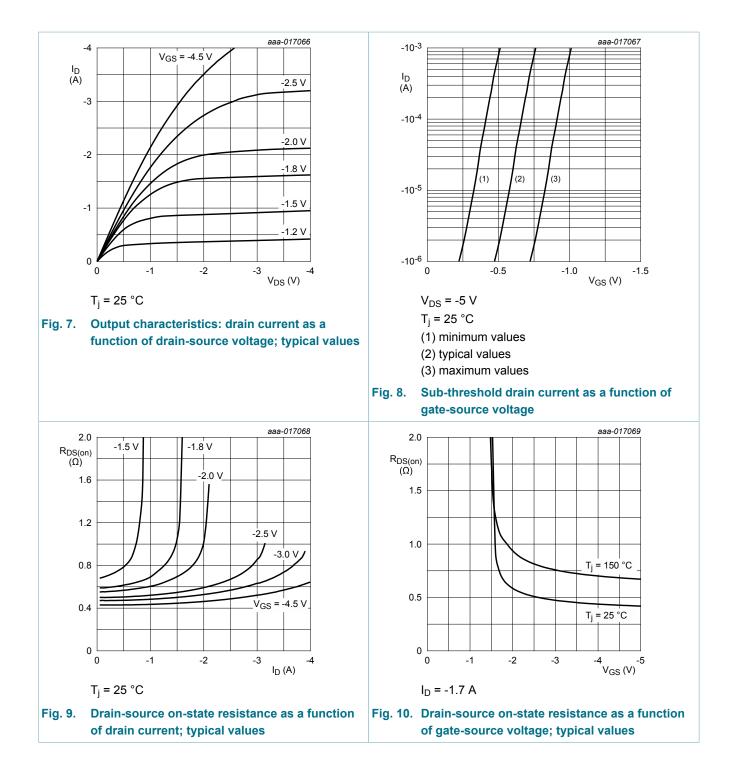
## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	5	μA
		$V_{GS}$ = -8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-5	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		$V_{GS}$ = 2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -1 A; T <sub>j</sub> = 25 °C	-	430	510	mΩ
		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -1 A; T <sub>j</sub> = 150 °C	-	680	810	mΩ
		$V_{GS}$ = -2.5 V; I <sub>D</sub> = -0.8 A; T <sub>j</sub> = 25 °C	-	570	770	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -0.25 A; T <sub>j</sub> = 25 °C	-	750	1140	mΩ
		$V_{GS}$ = -1.5 V; I <sub>D</sub> = -0.01 A; T <sub>j</sub> = 25 °C	-	950	1610	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -1 A; T <sub>j</sub> = 25 °C	-	2.1	-	S
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -15 V; I <sub>D</sub> = -1 A; V <sub>GS</sub> = -4.5 V;	-	1.4	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.3	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -15 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	122	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	11	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	9	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -15 V; I <sub>D</sub> = -1 A; V <sub>GS</sub> = -4.5 V;	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	22	-	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-drai	in diode	1	I	1		
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -0.7 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-1	-1.2	V

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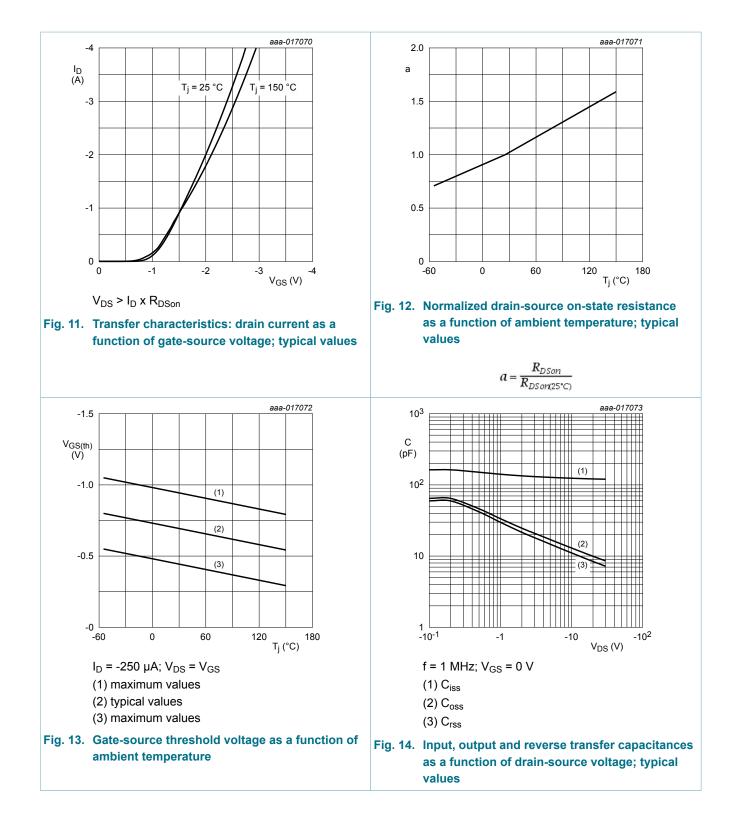
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#### 30 V, P-channel Trench MOSFET



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#### 30 V, P-channel Trench MOSFET

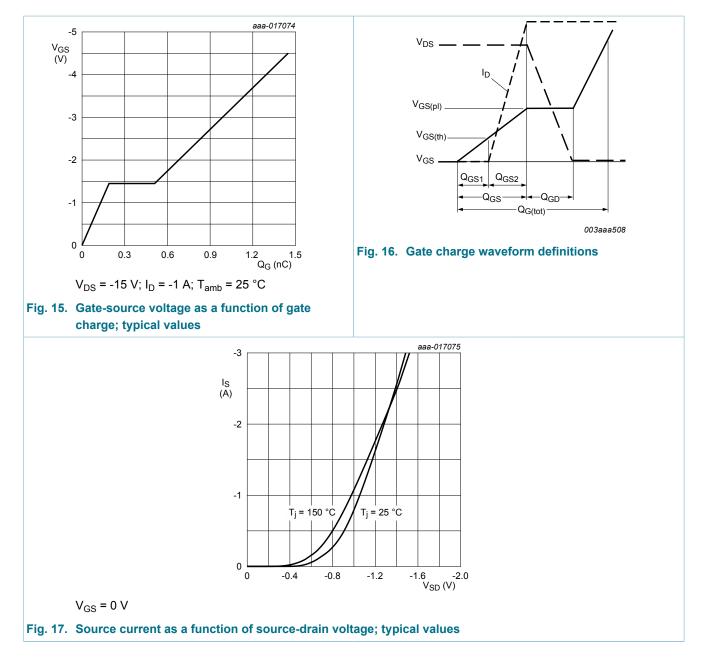


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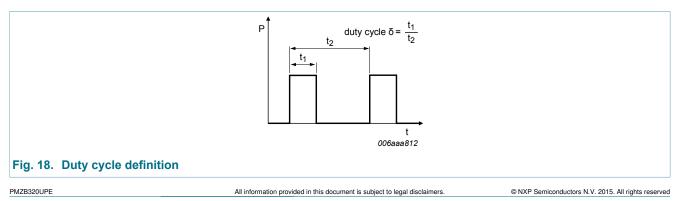
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#### 30 V, P-channel Trench MOSFET

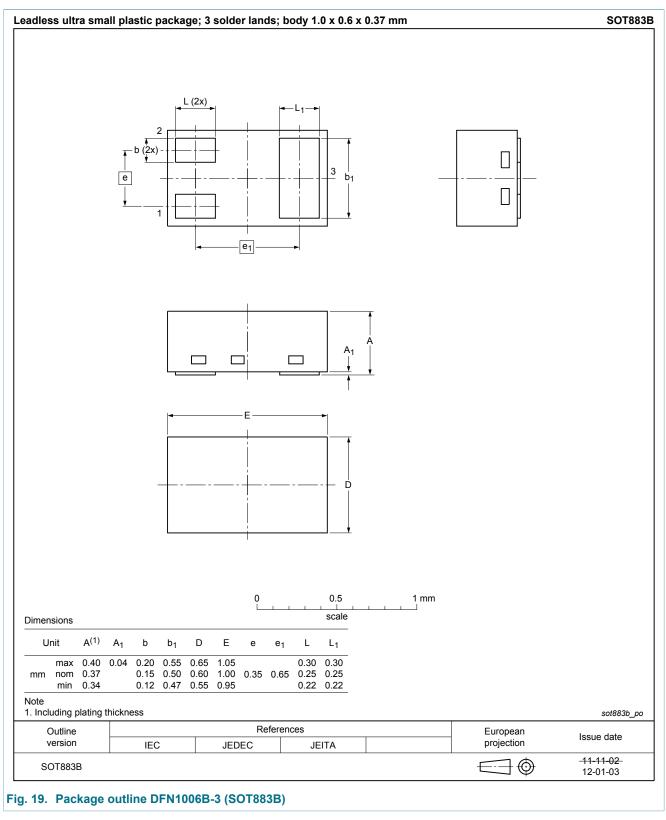


## **11. Test information**



30 V, P-channel Trench MOSFET

#### **12. Package outline**



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#### **13. Soldering**

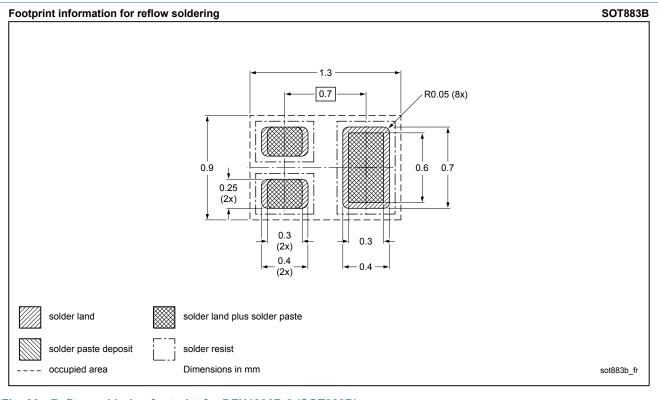


Fig. 20. Reflow soldering footprint for DFN1006B-3 (SOT883B)

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## 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMZB320UPE v.1	20150324	Product data sheet	-	-		

#### 30 V, P-channel Trench MOSFET

#### 15. Legal information

#### 15.1 Data sheet status

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Document status [ <u>1][2]</u>	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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